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CONFIRMATION NO. 5622

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APPLICANTS									
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** CONTINUING DATA **********************************									
This application is a DIV of 09/946,898 09/05/2001 PAT 6,746,942									
** FOREIGN APPLICATIONS ************************************									
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JAPAN P2000-269274 09/05/2000 JAPAN P2000-269261 09/05/2000 JAPAN P2001-244163 08/10/2001									
Foreign Priority claim	ed 🗹 v	es 🗆 no							
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Acknowledged Examiner's Signature Ipitfals ADDRESS 26263									
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